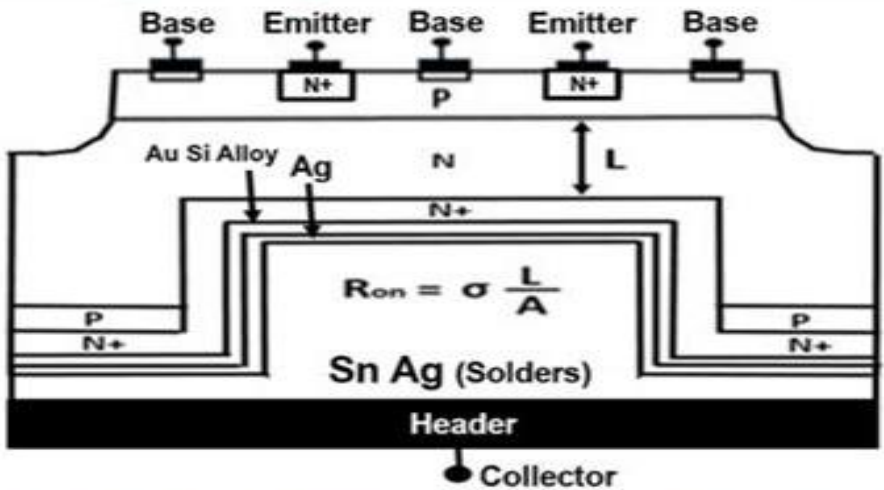
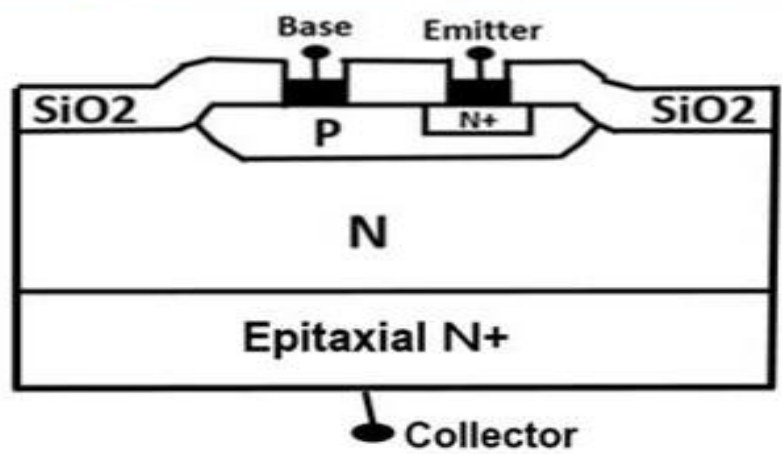


Acknowledgements

(1) Kawana, Yoshiyuki at Sony invented the low collector On-Resistance P+NP junction type Bipolar transistor by thinning the back side of silicon wafer,



(2) Kato, Toshio at Sony invented the silicon surface light etching and new SiO2 Passivation technique



Masaru Ibuka with Dr. Dr. John Bardeen visiting Sony in Tokyo , 1990



Yoshiyuki Kawan the inventor of Sony Power Bipolar Transistor.

